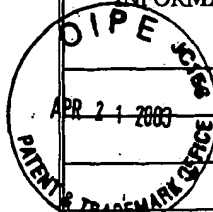


U.S. Department of Commerce, Patent and Trademark				Atty Docket No.		Application No.		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				SNDK.111US1 (formerly M-10237-1P US)		09/925,134		
				Applicants				
				Eliyahou Harari et al.				
				Filing Date		Group		
				August 8, 2001		2814		
<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>KL</i>		5,949,101	Sep. 7, 1999	Aritome				
<i>KL</i>		6,037,221	Mar. 14, 2000	Lee et al.				
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<b>Foreign Patent Documents</b>								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
<i>KL</i>		WO 97/32309	4 Sep. 1997	WIPO			X	
<i>KL</i>		0 601 747 A2	15 Jun. 1994	EPO			X	
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
<i>KL</i>		"Notification of Transmittal of the International Search Report or the Declaration", European Patent Office, International Searching Authority, January 29, 2003, 7 pages.						
Examiner <i>Kcwh/Dunbar</i>				Date Considered <i>9/19/03, 4/21/04</i>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								



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U.S. Department of Commerce, Patent and Trademark INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) JAN 12 2004 PATENT & TRADEMARK	Atty. Docket No.	Application No.
	SNDK.111US1	09/925,134
	Applicants	Conf. No.
	Harari et al.	6957
	Filing Date	Group
	August 8, 2001	2826

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72	1	4,112,507	9/5/78	White et al.			
	2	5,070,032	12/3/91	Yuan et al.			
	3	5,095,344	3/10/92	Harari			
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		Document	Date	Country	Class	Subclass	Yes	No

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72	12	Chan et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," <i>IEEE Electron Device Letters</i> , Vol. EDL-8, No. 3, March 1987, pp. 93-95.						
72	13	Nozaki et al., "A 1-Mb EEPROM with MONOS Memory Cell for Semiconductor Disk Application," <i>IEEE Journal of Solid State Circuits</i> , Vol. 26, No. 4, April 1991, pp. 497-501.						
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				SNDK.111US1		09/925,134	
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RL	26	2002/0118574	8/29/02	Gongwer et al.			

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RL	27	DiMaria et al., "Electrically-Alterable Read-Only-Memory Using Si-rich SiO <sub>2</sub> Injectors and a Floating Polycrystalline Silicon Storage Layer," <i>J. Appl. Phys.</i> 52(7), July 1981, pp. 4825-4842.
RL	28	Hori et al., "A MOSFET with Si-Implanted Gate-SiO <sub>2</sub> Insulator for NonVolatile Memory Applications," <i>IEDM</i> 92, April 1992, pp. 469-472.

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